



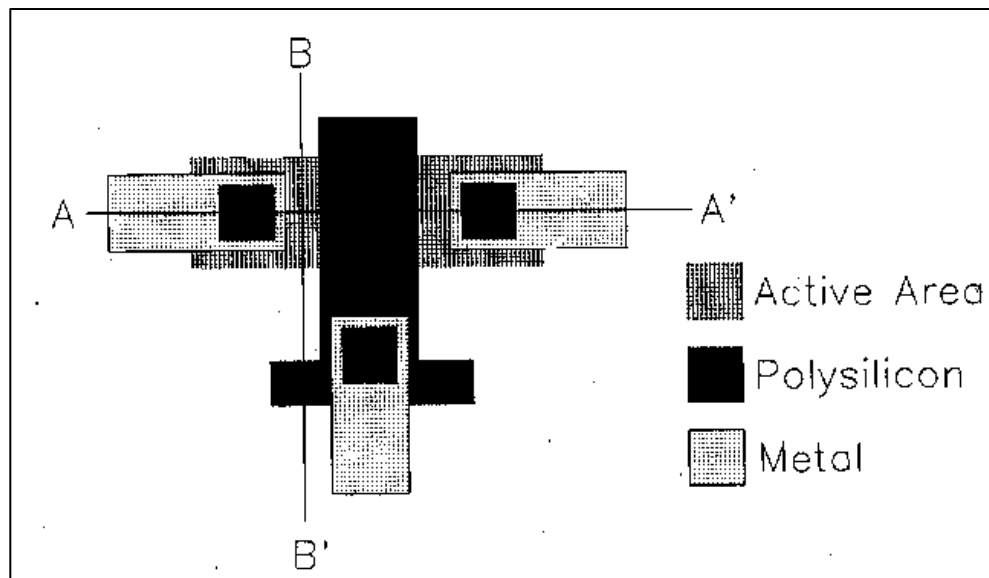
# Alexandria University

## Faculty of Engineering

Electrical Engineering Department

### Sheet 1 MOS Inverter Static Characteristics

- 1) Draw cross-sections of the following device along the lines A - A' and B - B'.



- 2) Consider CMOS inverter with the following parameters:

$$\text{NMOS} \quad V_{T0,n} = 0.6 \text{ V} \quad \mu_n C_{ox} = 60 \mu\text{A/V}^2 \quad (W/L)_n = 8$$

$$\text{PMOS} \quad V_{T0,p} = 0.7 \text{ V} \quad \mu_p C_{ox} = 25 \mu\text{A/V}^2 \quad (W/L)_p = 12$$

Calculate the noise margins and the switching threshold ( $V_{th}$ ) of this circuit. The power supply is  $V_{DD} = 3.3 \text{ V}$ .

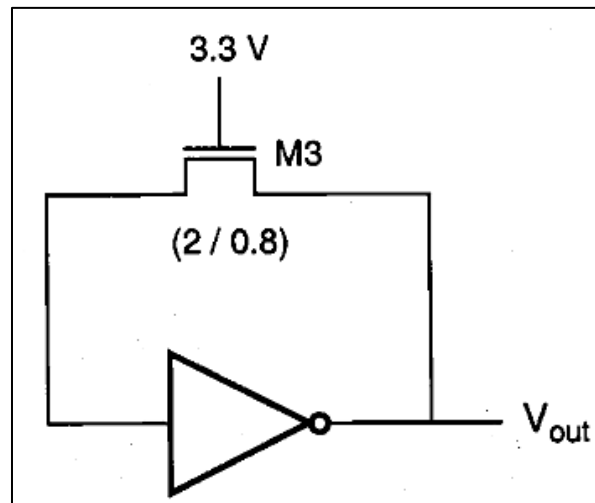
3) Design of a CMOS inverter circuit:

Use the same device parameters as in problem 2.

The power supply  $V_{DD} = 3.3 \text{ V}$ . The channel length of both transistors is  $L_n = L_p = 0.8 \text{ }\mu\text{m}$ .

- a) Determine the  $(W_n/W_p)$  ratio so that the switching (inversion) threshold voltage of the circuit is  $V_{th} = 1.4 \text{ V}$ .
- b) The CMOS fabrication process used to manufacture this inverter allows a variation of the  $V_{T0,n}$  value by  $\pm 15\%$  around its normal value, and a variation of the  $V_{T0,p}$  value by  $\pm 20\%$  around its normal value. Assuming that all other parameters (such as  $\mu_n, \mu_p, C_{ox}, W_n, W_p$ ) always retain their nominal values, find the upper and lower limits of the switching threshold voltage ( $V_{th}$ ) of this circuit.

4) Consider the CMOS inverter designed in problem 3, with the following circuit configuration



- a) Calculate the output voltage level  $V_{out}$ .
- b) Determine if the process-related variation of  $V_{T0,n}$  of M3 has any influence upon the voltage  $V_{out}$ .
- c) Calculate the total current being drawn from the power supply source, and determine its variation due to process-related threshold voltage variations.

5) Consider a CMOS inverter, with the following device parameters:

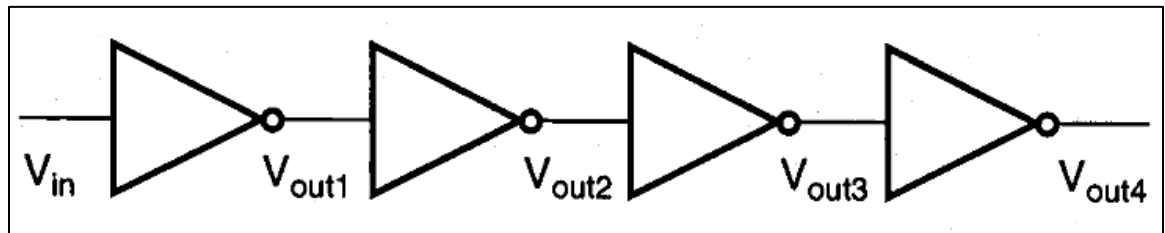
$$\text{NMOS} \quad V_{T0,n} = 0.6 \text{ V} \quad \mu_n C_{ox} = 60 \mu\text{A}/\text{V}^2$$

$$\text{PMOS} \quad V_{T0,p} = -0.8 \text{ V} \quad \mu_p C_{ox} = 20 \mu\text{A}/\text{V}^2$$

Also:  $V_{DD} = 3$   $\lambda = 0$

- Determine the (W/L) ratios of the NMOS and the PMOS transistor such that the switching threshold is  $V_{th} = 1.5 \text{ V}$ .
- Plot the VTC of the CMOS inverter using SPICE.
- Determine the VTC of the inverter for  $\lambda = 0.05$  and  $\lambda = 0.1 \text{ V}^{-1}$ .
- Discuss how the noise margins are influenced by non-zero  $\lambda$  value. Note that transistors with very short channel lengths tend to have larger  $\lambda$  values than long-channel transistors.

6) Consider the CMOS inverter designed in problem 5 above, with  $\lambda = 0.1 \text{ V}^{-1}$ . Now consider a cascade connection of four identical inverters, as shown.



- If the input voltage is  $V_{in} = 1.55 \text{ V}$ , find  $V_{out1}$ ,  $V_{out2}$ ,  $V_{out3}$  and  $V_{out4}$ .  
(note that this requires solving KCL equations for each subsequent stage, using the non-zero  $\lambda$  value).
- How many stages are necessary to restore a true logic output level?
- Verify your result with SPICE simulation.